

**IN THE CLAIMS:**

(1) Please amend Claim 1 as follows:

- Sub B1  
A'
1. (Amended) A process for manufacturing an integrated circuit package comprising:
- (a) forming a substrate having a first dielectric layer, a conductive layer having a first region insulated from a second region and located above the first dielectric layer, and a second dielectric layer above the conductive layer, the second dielectric layer having a cavity wherein the first and second regions are exposed within the cavity; and
- (b) interconnecting a first lead of an integrated circuit to the exposed first region and interconnecting a second lead of the integrated circuit to the exposed second region.

Sub B2  
A

(2) Please amend Claim 7 as follows:

7. (Amended) A method of manufacturing a substrate adapted to receive an integrated circuit chip comprising:
- (a) forming a first dielectric layer on a substrate;
- (b) forming a conductive layer having a first region insulated from a second region, above the first dielectric layer;
- (c) forming a second dielectric layer above the conductive layer; and
- (d) forming a cavity in the second dielectric layer to expose the first and second regions of the conductive layer and coupling a first lead of the integrated circuit chip to the exposed first region and coupling a second lead of the integrated circuit to the exposed second region.

(3) Please amend Claim 12 as follows:

A<sup>3</sup> 12. (Amended) The method recited in Claim 7, further comprising coupling the integrated circuit chip to the substrate.

(4) Please amend Claim 13 as follows:

13. (Amended) A method of manufacturing a substrate adapted to receive an integrated circuit chip comprising:

- A<sup>4</sup>
- (a) forming a first dielectric layer on a substrate;
  - (b) forming a conductive layer having a first region insulated from a second region, above the first dielectric layer;
  - (c) forming a second dielectric layer above the conductive layer;
  - (d) forming a second conductive layer above the second dielectric layer; and
  - (e) forming a cavity in a first region of the second dielectric layer to expose the first and second regions of the first conductive layer and coupling a first lead of the integrated circuit chip to the exposed first region and a second lead of the integrated circuit chip to the exposed second region.

(5) Please amend Claim 16 as follows:

A<sup>5</sup> 16. (Amended) The method recited in Claim 13, further comprising coupling the integrated circuit chip to the substrate.

(6) Please cancel Claim 17 without prejudice or disclaimer.